

NTE389 Silicon NPN Transistor Horizontal Output

Description:

The NTE389 is a high voltage silicon NPN power transistor in a TO3 type case designed for use in CRT horizontal deflection circuits.

Features:

- Collector–Emitter Voltage: $V_{CEX} = 1500V$
- Glass Passivated Base–Collector Junction
- Forward Bias Safe Operating Area @ $50\mu s = 20A, 300V$
- Switching Times with Inductive Loads: $t_f = 0.5\mu s$ (Typ) @ $I_C = 3A$

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	750V
Collector–Emitter Voltage, V_{CEX}	1500V
Emitter–Base Voltage, V_{EBO}	5V
Continuous Collector Current, I_C	4A
Continuous Base Current, I_B	3A
Continouos Emitter Current, I_E	7A
Total Power Dissipation, P_D	
$T_C = +25^\circ C$	100W
$T_C = +100^\circ C$	40W
Derate Above $+25^\circ C$	0.8W/ $^\circ C$
Operating Junction Temperature Range, T_J	-65° to $+150^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ C$
Thermal Resistance, Junction–to–Case, R_{thJC}	1.25 $^\circ C/W$
Maximum Lead Temperature (For Soldering, 1/8" from Case for 5sec), T_L	$+275^\circ C$

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics (Note 1)						
Collector–Emitter Sustaining Voltage	$V_{CE(sus)}$	$I_C = 50\text{mA}$, $I_B = 0$	750	–	–	V
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500\text{V}$, $V_{BE} = 0$	–	–	1.0	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}$, $I_C = 0$	–	–	1.0	mA
ON Characteristics (Note 1)						
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 3\text{A}$, $I_B = 1.2\text{A}$	–	–	5.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 3\text{A}$, $I_B = 1.2\text{A}$	–	–	1.5	V
Dynamic Characteristics						
Current Gain – Bandwidth Product	f_T	$I_C = 0.1\text{A}$, $V_{CE} = 5\text{V}$, $f_{\text{test}} = 1\text{MHz}$	–	4	–	MHz
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}$, $I_E = 0$, $f = 0.1\text{MHz}$	–	90	–	pF
Switching Characteristics						
Fall Time	t_f	$I_C = 3\text{A}$, $I_{B1} = 1.2\text{A}$, $L_B = 8\mu\text{H}$	–	0.5	1.0	μs

Note 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle = 2%.

